



PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q95169

Koji KUDO, et al.

Appln. No.: 10/580,560

Group Art Unit: Not Yet Assigned

Confirmation No.: Not Yet Assigned

Examiner: Not Yet Assigned

Filed: May 26, 2006

For: DISTRIBUTED-FEEDBACK SEMICONDUCTOR LASER, DISTRIBUTED-FEEDBACK SEMICONDUCTOR LASER ARRAY, AND OPTICAL MODULE

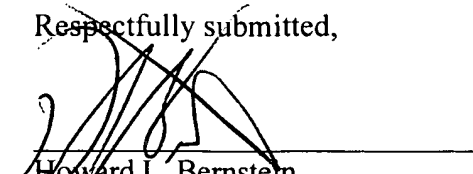
LETTER CONCERNING PTO/SB/08 A & B

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Applicants respectfully submit this letter to correct two typographical errors on the PTO/SB/08 A & B submitted with the Information Disclosure Statement filed on May 26, 2006, in the above-identified application. The reference listed as United States Patent No. 4,470,987, should have read United States Patent No. 4,740,987. The reference listed as Japanese Patent Publication No. 2002-198311, should have read Japanese Patent Publication No. 2002-198611. The reference listed as Japanese Patent No. 254994, should have read Japanese Patent No. 2545994. Attached is a corrected PTO/SB/08 A & B for the Examiner to initial upon consideration of all of the references submitted on May 26, 2006.

Respectfully submitted,


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WASHINGTON OFFICE

23373

CUSTOMER NUMBER

Date: January 24, 2007



Substitute for Form 1449 A & B/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Complete if Known

Application Number	10/580,560
Confirmation Number	Not yet assigned
Filing Date	May 26, 2006
First Named Inventor	Koji KUDO
Art Unit	Not yet assigned
Examiner Name	Not yet assigned
Attorney Docket Number	Q95169

Sheet 1 of 1

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² (if known)		
		US 4,740,987	A	04-26-1988	McCall, Jr. et al.
		US 4,796,273	A	01-03-1989	Yamaguchi
		US 2003/0021319	A1	01-30-2003	Aoki
		US 2002/0159705	A1	10-31-2002	Naniwae

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation ⁶
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)			
		JP	63-80590	A	04-11-1988		
		JP	3-283483	A	12-13-1991		
		JP	62-112391	A	05-23-1987		
		JP	2002-198611	A	07-12-2002		
		JP	63-62390	A	03-18-1988		
		JP	8-186334	A	07-16-1996		
		JP	2624140	B2	04-11-1997		
		JP	2003-46190	A	02-14-2003		
		JP	2545994	B2	08-08-1996		

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation ⁶
		M. Aoki et al., "85°C - 10Gbit/s Operation of 1.3-μm InGaAlAs MQW-DFB Laser", ECOC2000 Vol. 1, pp. 123-124.	
		K. Nakahara et al., "115°C, 12.5-Gb/s Direct Modulation of 1.3-μm InGaAlAs-MQW RWG DFB Laser with Notch-Free Grating Structure for Datacom Applications", OFC2003 PDP40.	
		G. Shtengel et al., "High-speed Vertical-Cavity Surface Emitting Laser", IEEE Photonic Technology Letters, 1993, vol. 5, no. 12, pp. 1359-1362.	
		A. Ramakrishnan et al., "Electrically Pumped 10 Gbit/s MOVPE-Grown Monolithic 1.3 μm VCSEL with GaInNAs Active Region", IEE Electronics Letters, 2002, Vol. 38, No. 7.	
		M. Uchida et al., "An AlGaAs Laser with High-Quality Dry Etched Mirrors Fabricated Using an Ultrahigh Vacuum in Situ Dry Etching and Deposition Processing System", IEEE Journal of Quantum Electronics, 1998, vol. 24, no. 11, pp. 2170-2176.	
		Y. Itaya et al., "Low Threshold Current GaInAsP/InP DFB Lasers", IEEE Journal of Quantum Electronics, Vol. QE-23, No. 6, June 1987, pp. 828-834.	
		T. Aoyagi et al., "Recent Progress of 10Gb/s Laser Diodes for Metropolitan Area Networks", SPIE, 2001, vol. 4580, APOC 2001, Beijing, China.	
		T. Yuasa et al., "Performance of Dry-Etched Short Cavity GaAs/AlGaAs Multiquantum-Well Lasers", Journal of Applied Physics, 1998, vol. 63, no. 5, pp. 1321-1327.	

Examiner Signature	Date Considered
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²See Kind Codes of USPTO Patent Documents at www.uspto.gov, MPEP 901.04 or follow the hyperlink from the title of the document to the intranet. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to indicate here if English language Translation is attached.